

Silicon NPN Power Transistors

2SC1195

DESCRIPTION

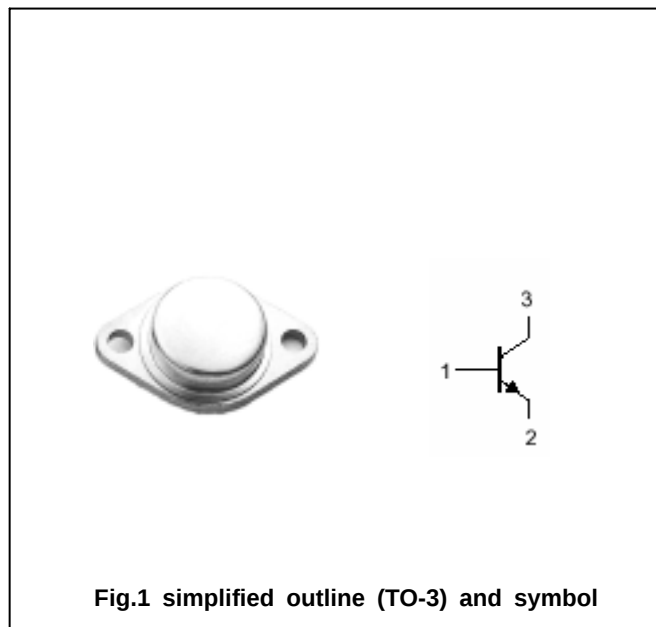
- With TO-3 package
- High power dissipation
- Low collector saturation voltage

APPLICATIONS

- For line operated audio output amplifier and switching power supply drivers applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2.5	A
P_C	Collector power dissipation	$T_C = 25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA ; I_B=0$	200			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2.5A ; I_B=0.5A$			1.5	V
V_{BE}	Base-emitter on voltage	$I_C=1A ; V_{CE}=5V$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=1A ; V_{CE}=5V$	30		150	

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PACKAGE OUTLINE

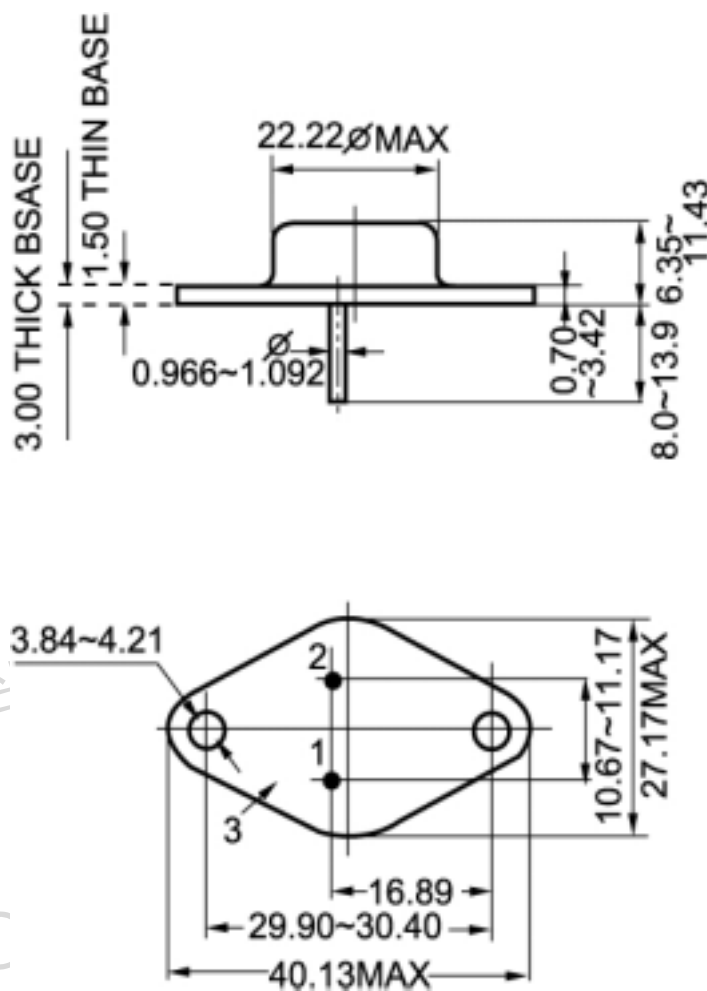


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)